



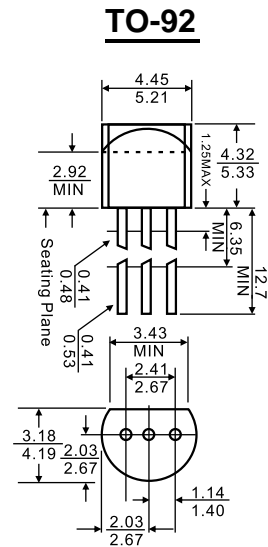
1. EMITTER
2. COLLECTOR
3. BASE

### Features

- ✧ Capable of being used in the low frequency to high frequency range.
- ✧ Large current capacity and wide ASO.

### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	-40	V
$V_{CE0}$	Collector-Emitter Voltage	-30	V
$V_{EB0}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-100	mA
$P_C$	Collector Power Dissipation	400	mW
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



Dimensions in inches and (millimeters)

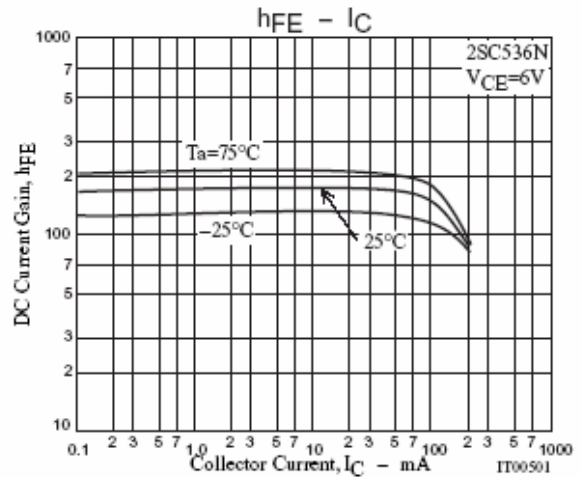
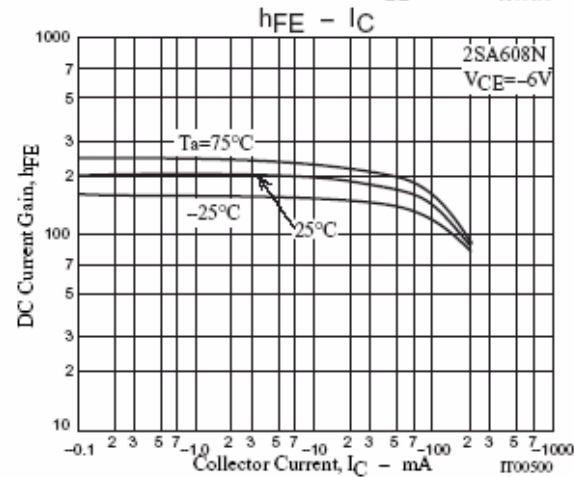
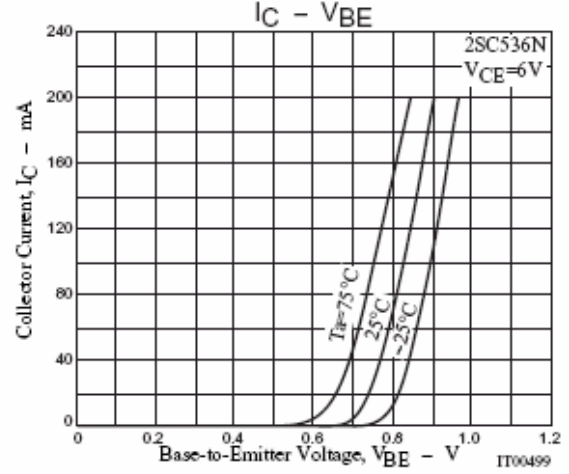
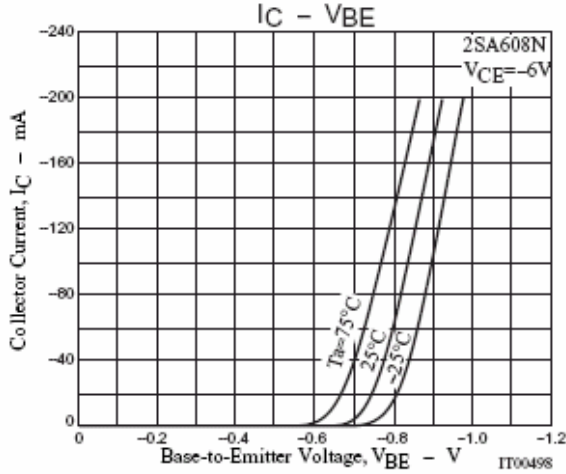
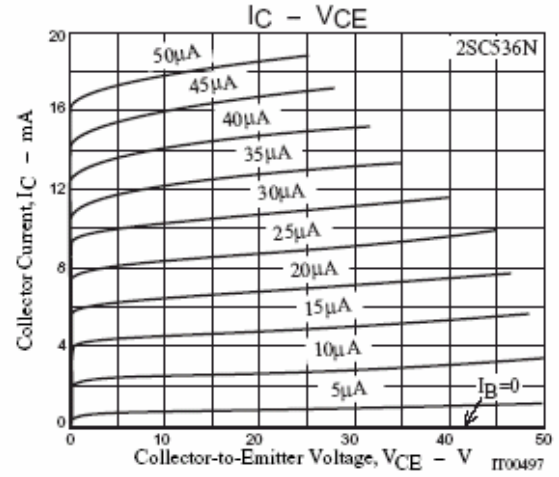
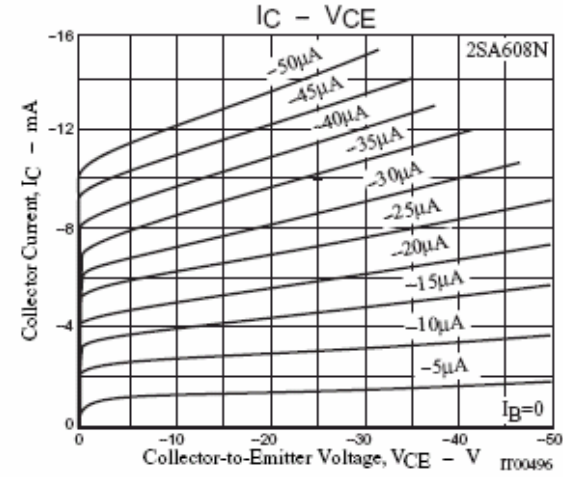
### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-100\mu\text{A}$ , $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C=-1\text{mA}$ , $I_B=0$	-30			V
Emitter-Base breakdown voltage	$V_{(BR)EB0}$	$I_E=-100\mu\text{A}$ , $I_C=0$	-5			V
Collector cut-off current	$I_{CB0}$	$V_{CB}=-25\text{V}$ , $I_E=0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB}=-4\text{V}$ , $I_C=0$			-1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-6\text{V}$ , $I_C=-1\text{mA}$	60		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}$ , $I_B=-5\text{mA}$			-0.5	V
Transition frequency	$f_T$	$V_{CE}=-6\text{V}$ , $I_C=-10\text{mA}$		180		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-6\text{V}$ , $f=1\text{MHz}$		7		pF

### CLASSIFICATION OF $h_{FE}$

Rank	D	E	F	G
Range	60-120	100-200	160-320	280-560

## Typical Characteristics



# 2SA608(PNP)

TO-92 Bipolar Transistors

